CLAIMS

 A ceramic substrate for apparatuses for use in semiconductor manufacture and/or inspection,

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- wherein the level of α -rays radiated from said ceramic substrate exceeds 0.25 c/cm²·hr and is not higher than 50 c/cm²·hr.
- The ceramic substrate according to claim 1, wherein said ceramic substrate has a temperature adjusting
 means.
 - 3. A ceramic heater, for heating a semiconductor, comprising a ceramic substrate and a heating element disposed on the surface or internally thereof,
 - wherein the level of α -rays radiated from said ceramic substrate exceeds 0.25 c/cm²-hr and is not higher than 50 c/cm²-hr.
 - 4. An electrostatic chuck comprising a ceramic substrate and electrodes embedded therein,
 - wherein the level of α -rays radiated from said ceramic substrate exceeds 0.25 c/cm²·hr and is not higher than 50 c/cm²·hr.
- 5. The electrostatic chuck according to claim 4, wherein said ceramic substrate has a temperature adjusting 25 means.
 - 6. A substrate for a wafer prober comprising a ceramic substrate and a conductor layer formed on the surface thereof, wherein the level of α -rays radiated from the surface of said ceramic substrate exceeds 0.25 c/cm²·hr and is not higher than 50 c/cm²·hr.
 - 7. The substrate for a wafer prober according to claim 6,
- 35 wherein said ceramic substrate has a temperature adjusting

means.